Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO247 plastic package.

2. Features and benefits

- Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- · Low leakage current
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- UPS
- EV Charger
- · Welding Machine
- Air Conditioner

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Values | | | | Unit |
|------------------|-------------------------------------|---|-------------|---|-----|------|------|
| Absolute | maximum rating | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | 600 | | | | V |
| $I_{F(AV)}$ | average forward current | $δ = 0.5$; square-wave pulse; $T_{mb} \le 88$ °C; Fig. 1; Fig. 2; Fig. 3 | 75 | | | | А |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t_p = 25 μs; T_{mb} ≤ 88 °C; square-wave pulse | 150 | | | Α | |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | | | Α | | |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | | | Α | | |
| Symbol | Parameter | Conditions | Min Typ Max | | Max | Unit | |
| Static ch | aracteristics | | | | | | |
| V _F | forward voltage | I _F = 75 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 2.2 | 2.75 | V |
| | | I _F = 75 A; T _j = 150 °C; <u>Fig. 6</u> | - 1.6 2.1 | | 2.1 | V | |
| Dynamic | characteristics | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | | - | - | 50 | ns |

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
| | | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 42 | - | ns |
| | | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 106 | - | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------------------|--------------------|---|
| 1 | K | cathode | | K 14 A |
| 2 | Α | anode | | K - |
| mb | mb | mounting base; connected to cathod | K A TO247-2L | |

6. Ordering information

Table 3. Ordering information

| Type number | Package Name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|-----------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BYC75W-600P | TO247-2L | BYC75W-600PQ | Tube | 30 | TO247L-2L (L) | 12-Nov-2020 |
| | | | | | TO247P-2L (P) | 31-Mar-2023 |

7. Marking

Table 4. Marking codes

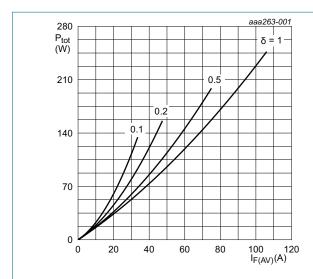
| Type number | Marking codes | | |
|-------------|------------------------------|------------------------------|--|
| | Assembly factory: L | Assembly factory: P | |
| BYC75W-600P | BYC75W 600P PJLxxxx xx | BYC75W 600P PJPxxxx xx | |

8. Limiting values

Table 5. Limiting values

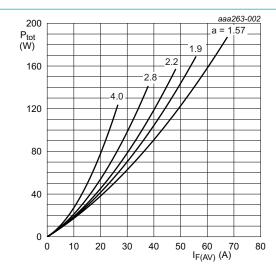
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|--------------------|-------------------------------------|--|------------|------|
| V_{RRM} | repetitive peak reverse voltage | | 600 | V |
| V_{RWM} | crest working reverse voltage | | 600 | V |
| V_R | reverse voltage | DC | 600 | V |
| I _{F(AV)} | average forward current | $δ = 0.5$; square-wave pulse; $T_{mb} \le 88$ °C; Fig. 1; Fig. 2; Fig. 3 | 75 | А |
| I _{FRM} | repetitive peak forward current | $δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 88 °C$; square-wave pulse | 150 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | 700 | А |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | 750 | А |
| T _{stg} | storage temperature | | -55 to 175 | °C |
| T _j | junction temperature | | -55 to 175 | °C |



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.547 \text{ V}; \text{ R}_s = 0.0074 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.547 V; R_s = 0.0074 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

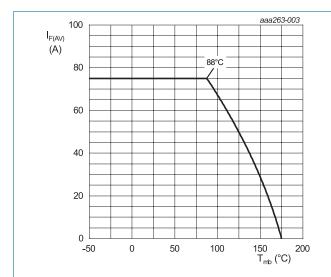


Fig. 3. Forward current as a function of mounting base temperature; typical values

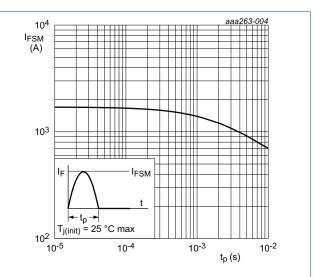


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | - | 0.44 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient free air | in free air | - | 45 | - | K/W |

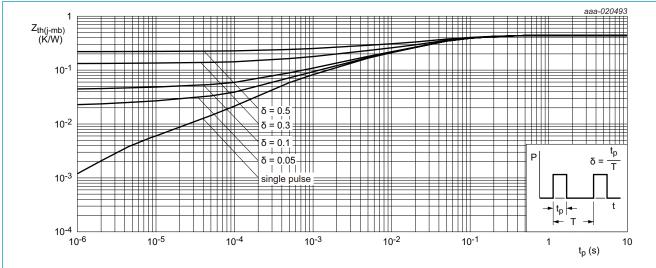
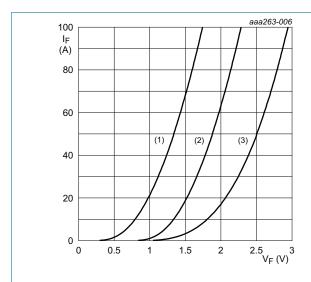


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7 Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------------|---|--|-----|------|--------|------|
| | aracteristics | | | -312 | 111007 | J 01 |
| V _F forward voltage | | I _F = 75 A; T _j = 25 °C; <u>Fig. 6</u> | - | 2.2 | 2.75 | V |
| | | I _F = 75 A; T _j = 150 °C; <u>Fig. 6</u> | - | 1.6 | 2.1 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _R = 600 V; T _j = 125 °C | - | - | 1 | mA |
| Dynamic | characteristics | | | | | |
| Q _r | reverse charge | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 85 | - | nC |
| | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 640 | - | nC | |
| t _{rr} reverse recovery time | | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | - | 50 | ns |
| | | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 42 | - | ns |
| | | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 106 | - | ns |
| I _{RM} | peak reverse recovery current | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 4.1 | - | А |
| | | $I_F = 75 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$ | - | 12.2 | - | А |
| E _{as} | non-repetitive avalanche energy | I _R = 1 A; L = 40 mH; T _{j(init)} = 25 °C | 20 | - | - | mJ |



 V_{o} = 1.547 V; R_{s} = 0.0074 Ω

(1) $T_j = 150 \, ^{\circ}\text{C}$; typical values

(2) T_i = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage

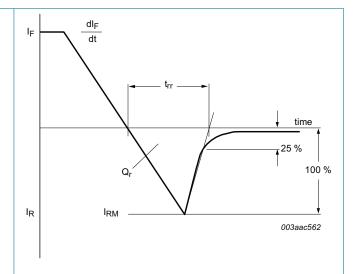
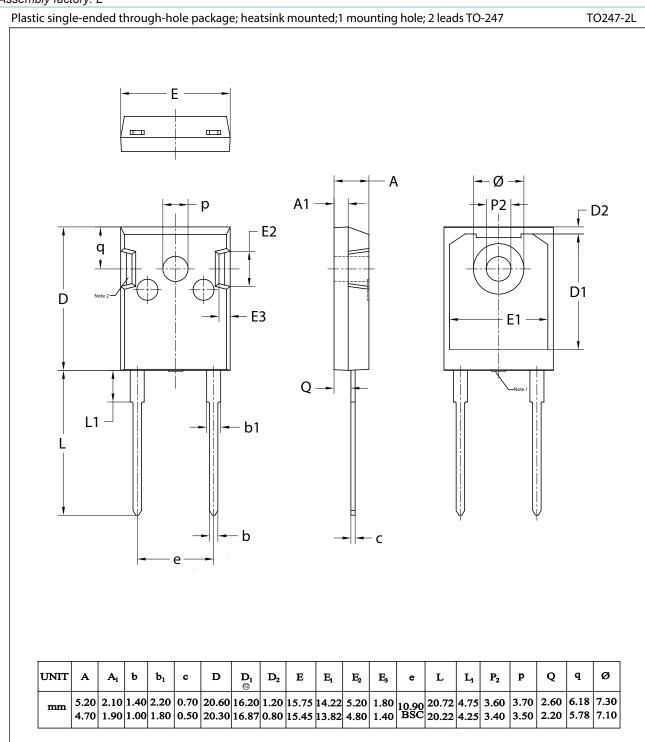


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

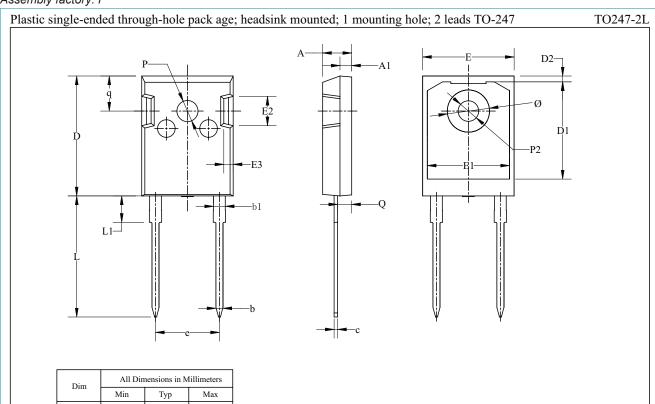
Assembly factory: L



Note:

Mold resin protrusion max 0.127mm. Metal exposed with Sn plating.

Assembly factory: P



| Dim | All Din | nensions in M | Iillimeters |
|-------|---------|---------------|-------------|
| Dilli | Min | Тур | Max |
| A | 4.70 | 4.95 | 5.20 |
| A1 | 1.90 | 2.00 | 2.10 |
| ь | 1.00 | 1.20 | 1.40 |
| b1 | 1.80 | 2.00 | 2.20 |
| с | 0.50 | 0.60 | 0.70 |
| D | 20.30 | 20.45 | 20.60 |
| D1 | 16.20 | 16.58 | 16.87 |
| D2 | 0.80 | 1.00 | 1.20 |
| Е | 15.45 | 15.60 | 15.75 |
| E1 | 13.82 | 14.02 | 14.22 |
| E2 | 4.80 | 5.00 | 5.20 |
| E3 | 1.40 | 1.60 | 1.80 |
| e | | 10.90 BSC | |
| L | 20.40 | 20.65 | 20.90 |
| L1 | 4.25 | 4.50 | 4.75 |
| P2 | 3.40 | 3.50 | 3.60 |
| P | 3.50 | 3.60 | 3.70 |
| Q | 2.20 | 2.40 | 2.60 |
| q | 5.78 | 5.98 | 6.18 |
| Ø | 7.10 | 7.19 | 7.30 |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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For more information, please visit: http://www.ween-semi.com
For sales office addresses, please send an email to: salesaddresses@ween-semi.com
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